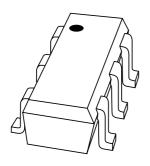
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# PUMZ1 NPN/PNP general purpose transistors

Product specification Supersedes data of 2002 May 6

2004 Oct 15





## **NPN/PNP** general purpose transistors

#### PUMZ1

#### **FEATURES**

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

#### **APPLICATIONS**

• General purpose switching and amplification.

#### **DESCRIPTION**

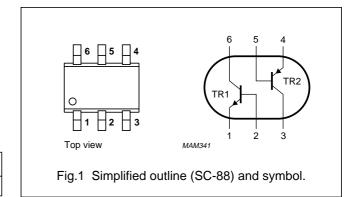
Two independently operating NPN/PNP transistors in an SC-88; SOT363 plastic package.

#### **MARKING**

TYPE NUMBER	MARKING CODE(1)	
PUMZ1	F*Z	

#### **PINNING**

PIN		DESCRIPTION
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
3, 6	collector	TR2; TR1



#### Note

- 1. \* = -: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

#### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE		
I THE NUMBER			VERSION
PUMZ1	_	plastic surface mounted package; 6 leads	SOT363

# NPN/PNP general purpose transistors

PUMZ1

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity					
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	_	40	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V	
Ic	collector current (DC)		_	100	mA	
I <sub>CM</sub>	peak collector current		_	200	mA	
I <sub>BM</sub>	peak base current		_	200	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device	Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW	

#### Note

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	416	K/W

#### Note

1. Device mounted on an FR4 printed-circuit board.

<sup>1.</sup> Device mounted on an FR4 printed-circuit board.

# NPN/PNP general purpose transistors

PUMZ1

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 30 V	_	100	nA
		I <sub>E</sub> = 0 A; V <sub>CB</sub> = 30 V; T <sub>j</sub> = 150 °C	_	10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 4 V	_	100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 6 V	120	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$	_	200	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0 A; V <sub>CB</sub> = 12 V; f = 1 MHz			
	TR1		_	1.5	pF
	TR2		_	2.2	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 12 V; f = 100 MHz	100	_	MHz

#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

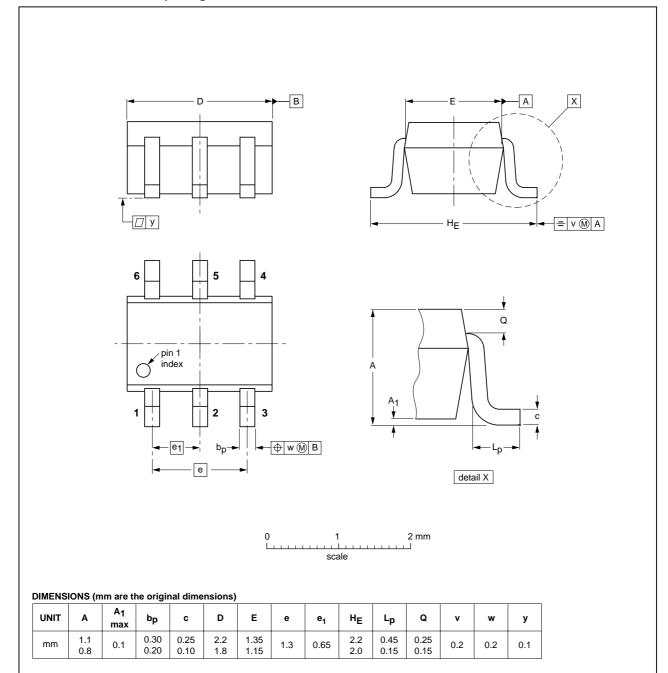
# NPN/PNP general purpose transistors

PUMZ1

#### **PACKAGE OUTLINE**

#### Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE	ITLINE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT363			SC-88			97-02-28

#### NPN/PNP general purpose transistors

PUMZ1

#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### **DEFINITIONS**

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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#### **Contact information**

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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